

WHAT IS CLAIMED IS:

1. A semiconductor device formed on a substrate, comprising:
an interconnection line formed on said substrate and provided to
structure a prescribed circuit; and
a fuse incorporated into said interconnection line,
5 said fuse and a connection portion of said interconnection line
electrically connected to the fuse being formed of different metals.
2. The semiconductor device according to claim 1, wherein
an oxidation speed of the metal forming said fuse is faster than an
oxidation speed of the metal forming the connection portion of said
interconnection line.
3. The semiconductor device according to claim 1, wherein
said fuse is formed of a copper metal, and
the connection portion of said interconnection line is formed of an
aluminum metal.
4. The semiconductor device according to claim 3, wherein
said fuse is formed of the copper metal formed in a damascene
process and planarized by a CMP (Chemical Mechanical Polishing) process.
5. The semiconductor device according to claim 1, wherein
said interconnection line is formed as a multilayer interconnection
line,
said fuse is provided at a same layer as one layer of the multilayer
5 interconnection line, and
an antireflection layer is provided closer to said substrate than a
layer of said fuse is.
6. The semiconductor device according to claim 5, wherein
said antireflection layer includes a first antireflection layer

extending in a direction of a length of said fuse, and a second antireflection layer extending in a direction traversing the first antireflection layer.

7. The semiconductor device according to claim 1, wherein said interconnection line is formed as a multilayer interconnection line,

5 said fuse is provided at a same layer as one layer of the multilayer interconnection line, and

a reflection layer is provided closer to said substrate than a layer of said fuse is.

8. The semiconductor device according to claim 7, wherein said reflection layer includes a dummy metal line provided between said fuses in a planar view and a transparent resin film covering the dummy metal line, said transparent resin film forming a recessed and protruded surface having a portion overlying the dummy metal line and projecting closer to said fuse than a portion between the dummy metal lines.

9. The semiconductor device according to claim 1, wherein said fuse is formed from at least two portions different in width.

10. A semiconductor device formed on a substrate, comprising: an interconnection line formed on said substrate and provided to structure a prescribed circuit; and

5 a fuse incorporated into said interconnection line, said fuse having a width gradually reduced from an end toward an intermediate portion of said fuse.

11. The semiconductor device according to claim 10, wherein said fuse has at least three different widths from the end toward the intermediate portion.